

Yuichi Fujita

List of Publications by Year in descending order

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papers

561
citations

623734

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all docs

36
docs citations

36
times ranked

331
citing authors

#	ARTICLE	IF	CITATIONS
1	Greatly enhanced generation efficiency of pure spin currents in Ge using Heusler compound Co_2FeSi electrodes. Applied Physics Express, 2014, 7, 033002.	2.4	65
2	Spin Transport and Relaxation up to 250ÅK in Heavily Doped n -Type Ge Detected Using Co_2FeSi . Physical Review Applied, 2017, 8, .	3.8	52
3	Spin transport and relaxation in germanium. Journal Physics D: Applied Physics, 2018, 51, 393001.	2.8	48
4	Giant Spin Accumulation in Silicon Nonlocal Spin-Transport Devices. Physical Review Applied, 2017, 8, .	3.8	47
5	Spin relaxation through lateral spin transport in heavily doped n -type silicon. Physical Review B, 2017, 95, .	3.2	38
6	Room-temperature spin transport in n-Ge probed by four-terminal nonlocal measurements. Applied Physics Express, 2017, 10, 093001.	2.4	31
7	Temperature-independent spin relaxation in heavily doped n -type germanium. Physical Review B, 2016, 94, .	3.2	30
8	Large impact of impurity concentration on spin transport in degenerate n -Ge. Physical Review B, 2017, 95, .	3.2	22
9	Nonlinear Electrical Spin Conversion in a Biased Ferromagnetic Tunnel Contact. Physical Review Applied, 2018, 10, .	3.8	21
10	Room-temperature detection of spin accumulation in silicon across Schottky tunnel barriers using a metal-oxide-semiconductor field effect transistor structure (invited). Journal of Applied Physics, 2013, 113, .	2.5	20
11	A crystalline germanium flexible thin-film transistor. Applied Physics Letters, 2017, 111, .	3.3	20
12	Crystal Growth in Laser Surface Melting and Cladding of Ni-Base Single Crystal Superalloy. Welding in the World, Le Soudage Dans Le Monde, 2008, 52, 64-78.	2.5	17
13	Correlation between spin transport signal and Heusler/semiconductor interface quality in lateral spin-valve devices. Physical Review B, 2018, 98, .	3.2	15
14	Room-temperature sign reversed spin accumulation signals in silicon-based devices using an atomically smooth $\text{Fe}_3\text{Si}/\text{Si}(111)$ contact. Journal of Applied Physics, 2013, 113, .	2.5	14
15	Finely Controlled Approaches to Formation of Heusler-Alloy/Semiconductor Heterostructures for Spintronics. Materials Transactions, 2016, 57, 760-766.	1.2	14
16	Nonmonotonic bias dependence of local spin accumulation signals in ferromagnet/semiconductor lateral spin-valve devices. Physical Review B, 2019, 100, .	3.2	14
17	Control of electrical properties in Heusler-alloy/Ge Schottky tunnel contacts by using phosphorous $\hat{\Gamma}$ -doping with Si-layer insertion. Materials Science in Semiconductor Processing, 2017, 70, 83-85.	4.0	12
18	Quantification of Spin Drift in Devices with a Heavily Doped n -Si Channel. Physical Review Applied, 2019, 11, .	3.8	12

#	ARTICLE	IF	CITATIONS
19	Room-Temperature Tunneling Magnetoresistance in Magnetic Tunnel Junctions with a $\text{D}_{0.3}\text{Fe}_{0.3}\text{Si}$ Electrode. Japanese Journal of Applied Physics, 2013, 52, 04CM02.	1.5	10
20	Hanle spin precession in a two-terminal lateral spin valve. Applied Physics Letters, 2019, 114, 242401.	3.3	10
21	Direct observation of imploded core heating via fast electrons with super-penetration scheme. Nature Communications, 2019, 10, 5614.	12.8	8
22	Effects of the atomic order on the half-metallic electronic structure in the $\text{C}_{1-x}\text{Mn}_x$		